



RT2 – LET calculation, ions penetration

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Main problems to discuss

- Various LET calculation methods.
- Range effects:
 - LET modifications due to DUT overlayers.
 - LET calculation at sensitive volume level (deep located sensitive volumes or back-side irradiation).
- Other problems when performing HI tests



Various LET/range calculation tools



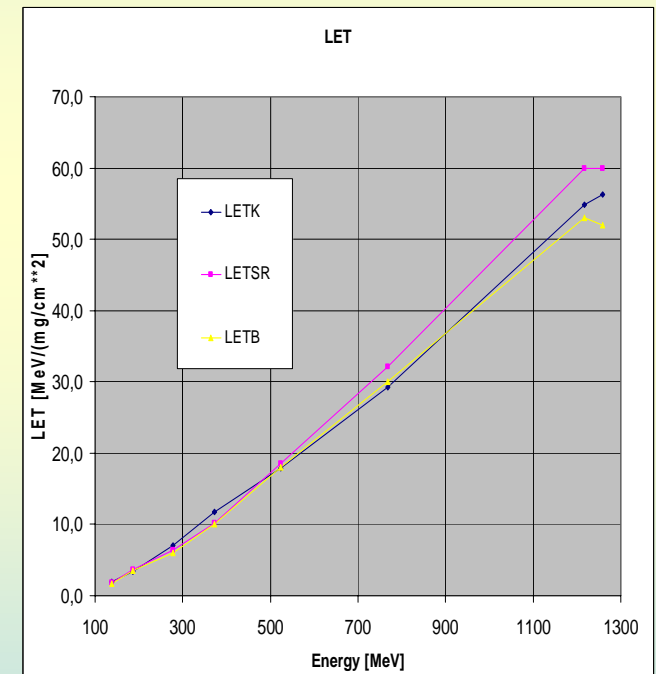
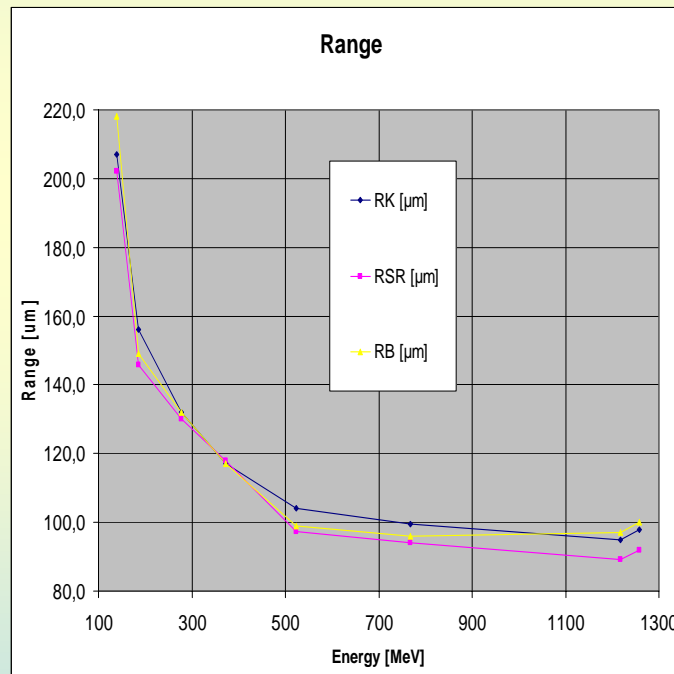
- SRIM, TRIM, Kantele, Hubert & al.,...

=>some non negligible differences!!!

e.g.: Kantele (K)

vs SRIM (S) &

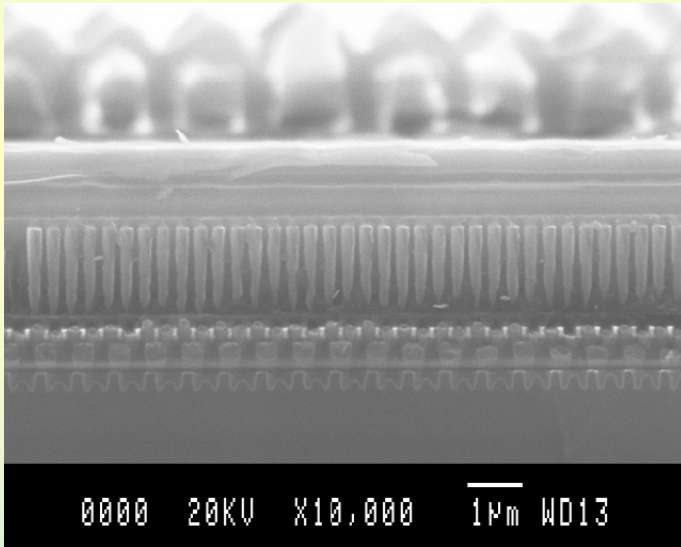
BNL LET calculator (B)



Is it possible to harmonize the LET/ range calculation methods?

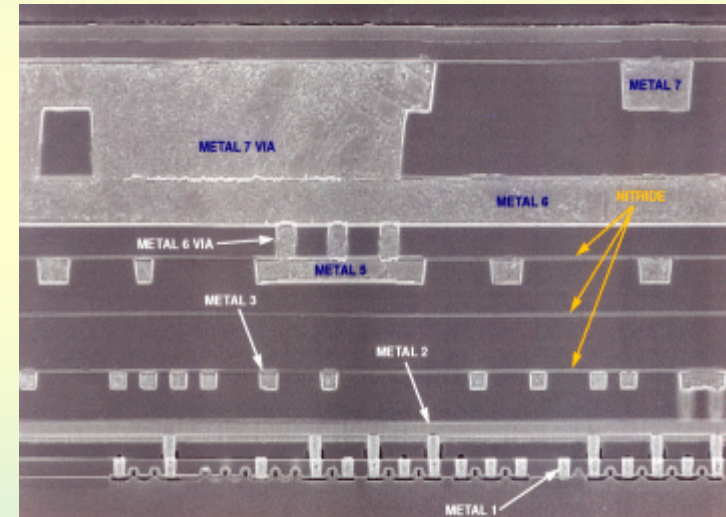
LET calculation at sensitive volume level

- Front side irradiation: Overlayer materials are not taken into account when calculating LET and range.



<< 256Mb SDRAM
(vertical storage capacitor).

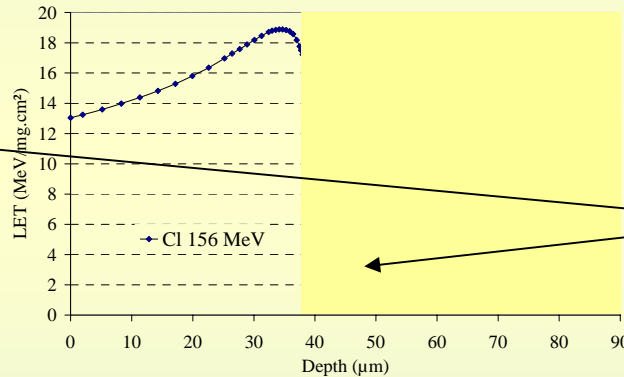
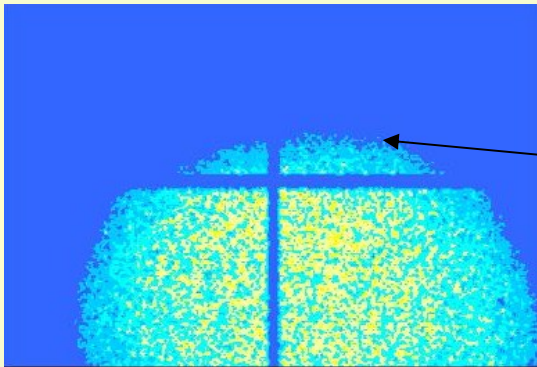
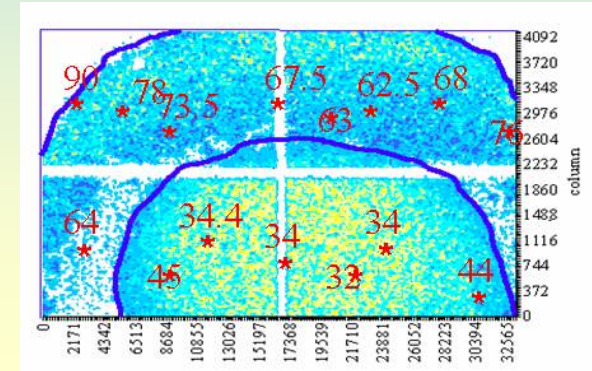
Planar Copper >>
7 Metal layers
Damascene technology



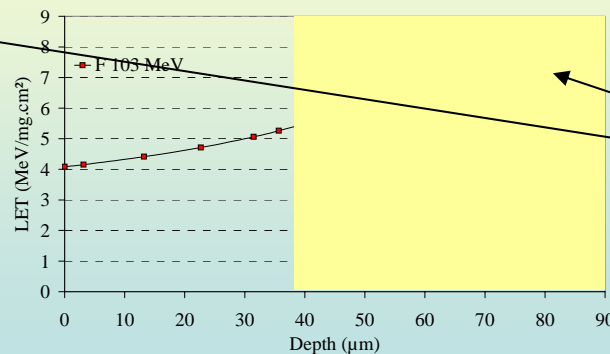
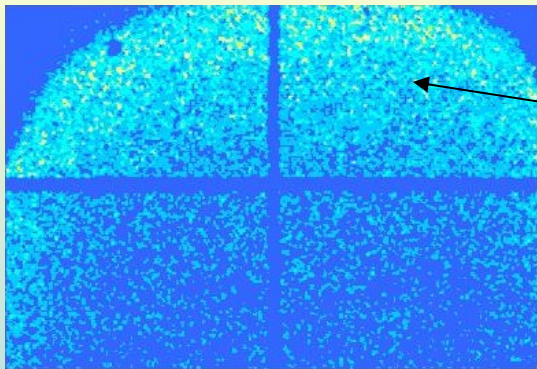
- Backside irradiation: After thinning, the die thickness may vary all over the DUT surface (a few μm only with up-to-date techniques). This shall be taken into account when choosing the ion.

LET calculation at sensitive volume level

Backside irradiation of 256Mbit SDRAM (2001)
=> Worst case: important thickness variation
and limited beam range.



Range
limitation



Enhanced LET
effect



Other problems



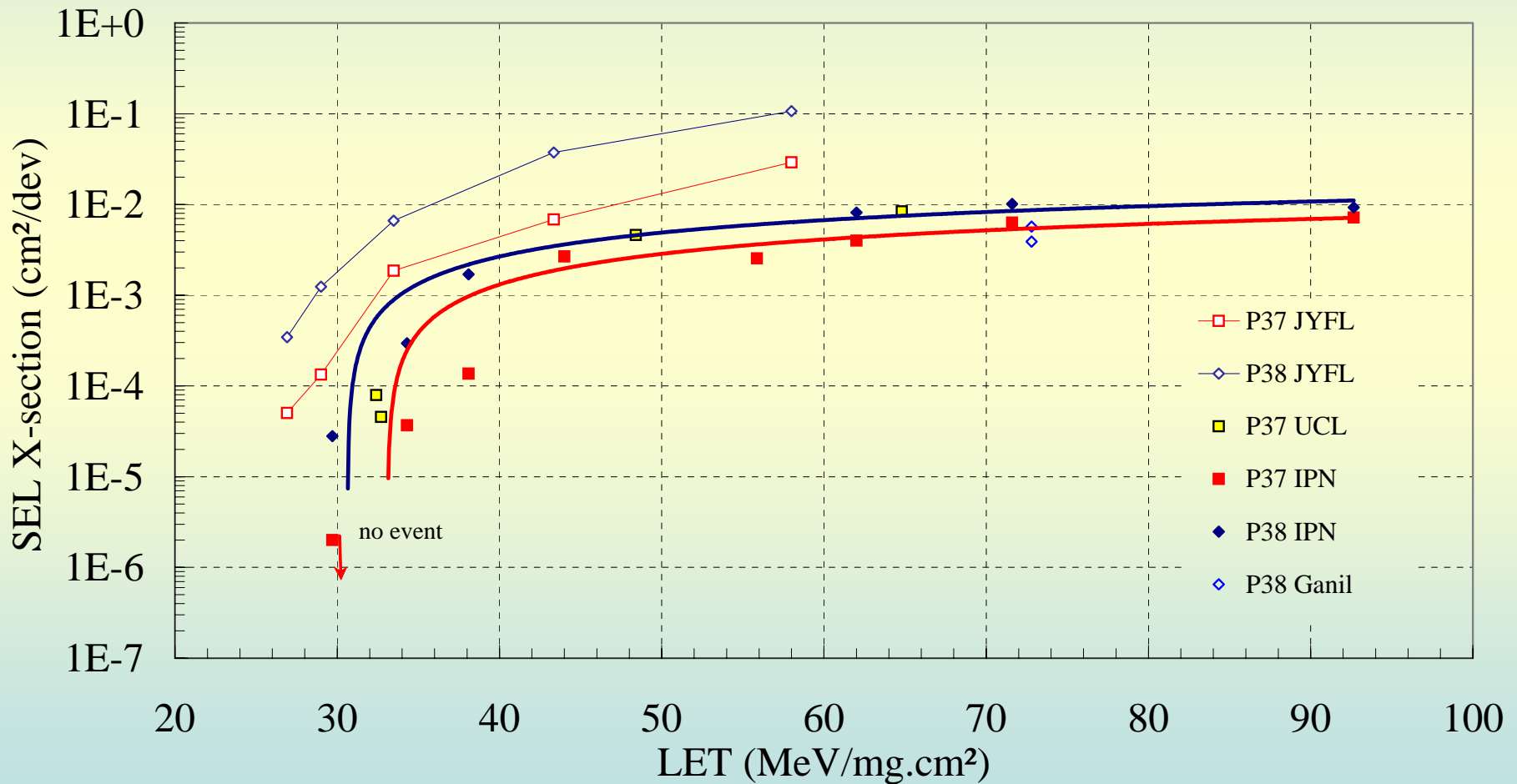
- Particle monitoring X-check between accelerators
 - Reproducibility between accelerators
(Differences can be observed even when testing the same DUT with the same test system and similar LET and range).
 - Reproducibility between test campaigns at the same facility.
- ⇒ Is the problem due to LET/range, dosimetry (counting, homogeneity, beam purity)?



Ex: 1M SRAM / SEL



IPN(>30 μ m)-UCL(>100 μ m)-JYFL(>100 μ m)-Ganil(>>100 μ m)



Beams LET/range comparison

